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Kind regards,

Team Nexperia

**PNP/PNP** resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$ 

Rev. 5 — 21 December 2011

**Product data sheet** 

## 1. Product profile

## **1.1 General description**

PNP/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1.	Product	overview

Type number	Package		-		Package
	NXP	JEITA	complement	complement	configuration
PEMB18	SOT666	-	PEMD18	PEMH18	ultra small and flat lead
PUMB18	SOT363	SC-88	PUMD18	PUMH18	very small

Reduces component count

AEC-Q101 qualified

Reduces pick and place costs

### **1.2 Features and benefits**

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design

### **1.3 Applications**

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-50	V
lo	output current		-	-	-100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	





1

2 3 006aaa212

#### PNP/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$

## 2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1	001aab555	

## 3. Ordering information

# Table 4. Ordering information Type number Package Name Description Version PEMB18 plastic surface-mounted package; 6 leads SOT666 PUMB18 SC-88 plastic surface-mounted package; 6 leads SOT363

## 4. Marking

Table 5.         Marking codes	
Type number	Marking code <sup>[1]</sup>
PEMB18	6A
PUMB18	B8*

[1] \* = placeholder for manufacturing site code

## **PNP/PNP** resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$

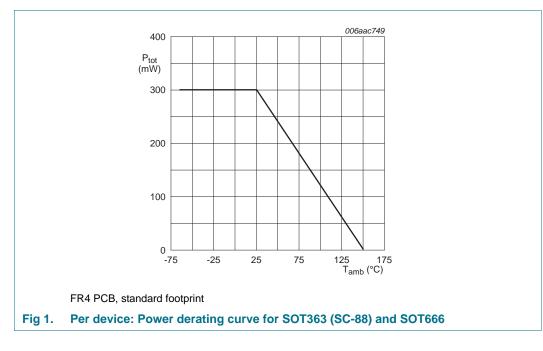
## 5. Limiting values

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	stor					
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-7	V
VI	input voltage					
	positive			-	+7	V
	negative			-	-20	V
lo	output current			-	-100	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	PEMB18 (SOT666)		[1][2]	-	200	mW
	PUMB18 (SOT363)		<u>[1]</u>	-	200	mW
Per device	;					
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	PEMB18 (SOT666)		[1][2]	-	300	mW
	PUMB18 (SOT363)		<u>[1]</u>	-	300	mW
Т <sub>ј</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	+150	°C
T <sub>stg</sub>	storage temperature			-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PNP/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$ 



## 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per transistor						
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air				
	PEMB18 (SOT666)		<u>[1][2]</u> _	-	625	K/W
	PUMB18 (SOT363)		<u>[1]</u> _	-	625	K/W
Per devic	e					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air				
	PEMB18 (SOT666)		[1][2] _	-	417	K/W
	PUMB18 (SOT363)		<u>[1]</u> _	-	417	K/W

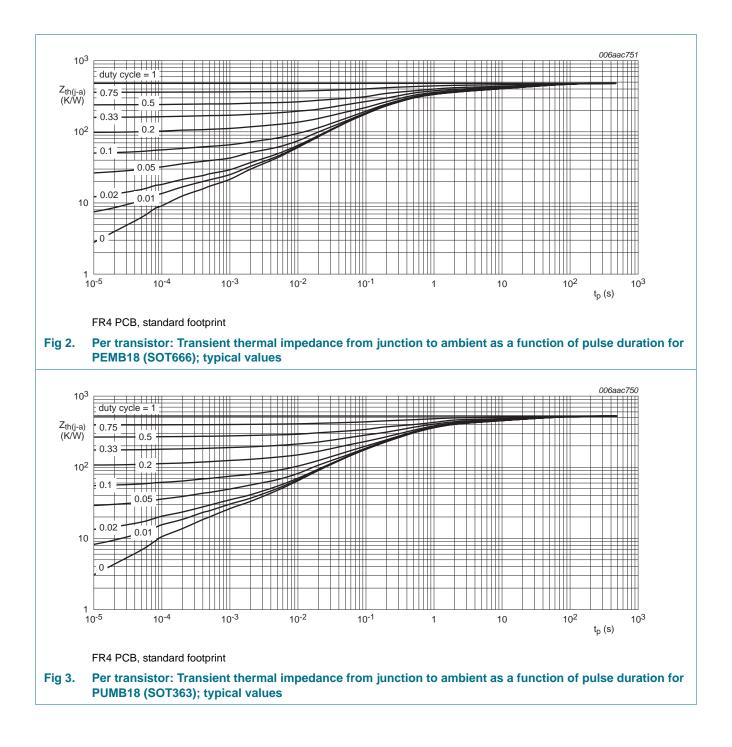
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PEMB18\_PUMB18 Product data sheet

## PEMB18; PUMB18

PNP/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$ 



**PNP/PNP** resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$ 

## 7. Characteristics

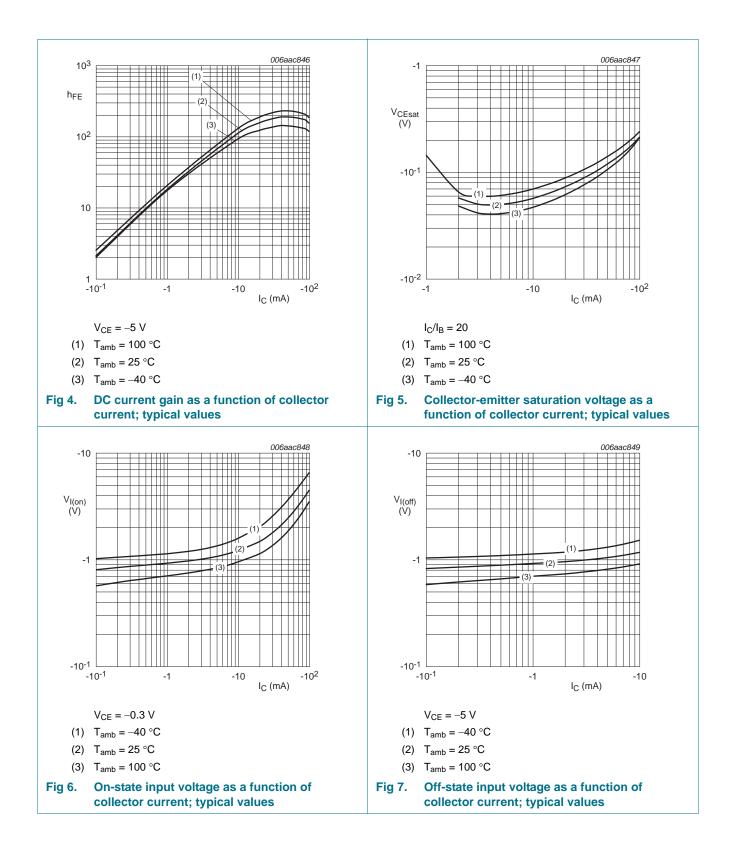
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off	$V_{CE}$ = -30 V; I <sub>B</sub> = 0 A	-	-	-1	μΑ
	current	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A};$ T <sub>j</sub> = 150 °C	-	-	-5	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-600	μA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -5 V; I <sub>C</sub> = -10 mA	50	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA}; I_{B} = -0.5 \text{ mA}$	-	-	-100	mV
V <sub>I(off)</sub>	off-state input voltage	$V_{CE}$ = –5 V; $I_{C}$ = –100 $\mu A$	-	-0.9	-0.3	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE} = -0.3 \text{ V};$ $I_C = -20 \text{ mA}$	-2.5	-1.5	-	V
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CE} = -5 V; I_C = -10 mA;$ f = 100 MHz	<u>1]</u> _	180	-	MHz

[1] Characteristics of built-in transistor

PEMB18\_PUMB18 Product data sheet

## PEMB18; PUMB18

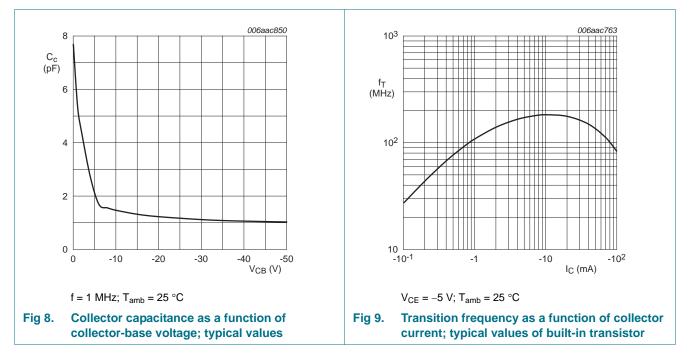
#### PNP/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$



PEMB18\_PUMB18 Product data sheet

## PEMB18; PUMB18

PNP/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$ 

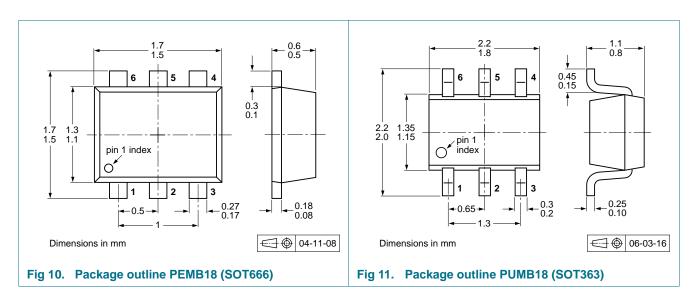


## 8. Test information

## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline



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PNP/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$ 

## **10. Packing information**

#### Table 9. Packing methods

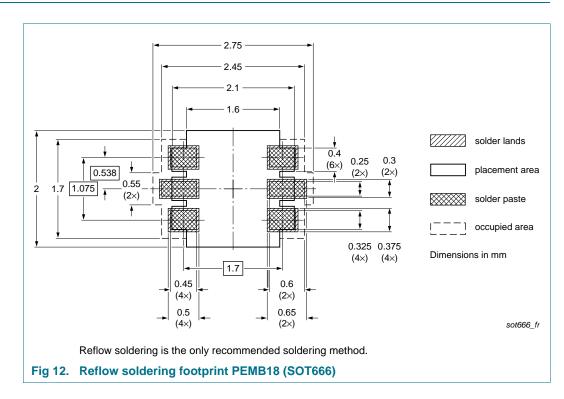
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Туре	Package Description			Packing quantity				
number				3000	4000	8000	10000	
PEMB18	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-	
		4 mm pitch, 8 mm tape and reel		-	-115	-	-	
PUMB18	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135	
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165	

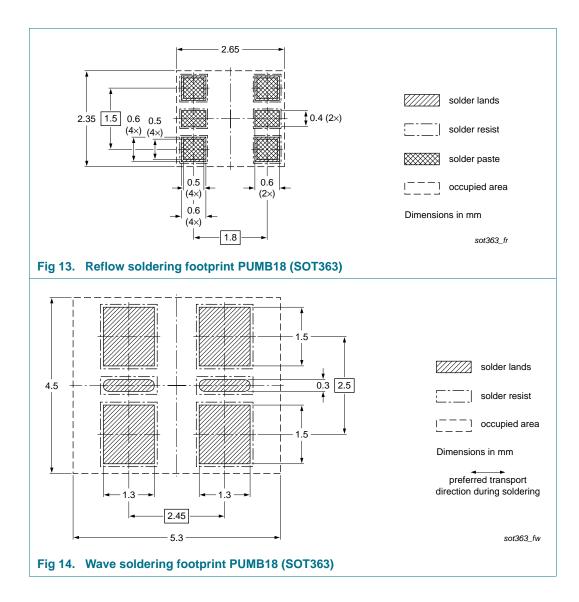
[1] For further information and the availability of packing methods, see Section 14.

- [2] T1: normal taping
- [3] T2: reverse taping

## 11. Soldering



PNP/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$ 



**PNP/PNP** resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$ 

## 12. Revision history

#### Table 10.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMB18_PUMB18 v.5	20111221	Product data sheet	-	PEMB18_PUMB18 v.4
Modifications:	<ul> <li>Section 4 "M</li> <li>Figure 1 to 3</li> <li>Section 6 "TI</li> <li>Figure 4 to 7</li> <li>Table 8 "Cha</li> <li>Section 8 "Te</li> <li>Section 11 "S</li> </ul>	roduct profile": updated arking": updated bermal characteristics": up c updated <u>aracteristics"</u> : I <sub>CEO</sub> and V <sub>CE</sub> est information": added <u>Soldering</u> ": added <u>Legal information</u> ": updated	<sub>isat</sub> updated, f <sub>T</sub> added	
PEMB18_PUMB18 v.4	20090901	Product data sheet	-	PEMB18_PUMB18 v.3
PEMB18_PUMB18 v.3	20050708	Product data sheet	-	PEMB18_PUMB18 v.2
PEMB18_PUMB18 v.2	20050202	Product data sheet	-	PUMB18 v.1
PUMB18 v.1	20031003	Product specification	-	-

PNP/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$ 

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PEMB18\_PUMB18

#### **PNP/PNP** resistor-equipped transistors; $R1 = 4.7 \text{ k}\Omega$ , $R2 = 10 \text{ k}\Omega$

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## PEMB18; PUMB18

**PNP/PNP** resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$ 

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